

A fast, primary Coulomb blockade thermometer

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We have measured the third derivative of the current-voltage characteristics, d^3I/dV^3 , in a two-dimensional array of small tunnel junctions using a lock-in amplifier. We show that this derivative is zero at a voltage which scales linearly with the temperature and depends only on the temperature and natural constants, thus providing a primary thermometer. We demonstrate a measurement method which extracts the zero crossing voltage directly using a feedback circuit. This method requires only one voltage measurement, which makes it substantially faster than the original Coulomb blockade thermometry method.

Coulomb blockade thermometry (CBT) [1, 2, 3] is a primary thermometry method which is suitable for cryogenic temperatures in the range 20 mK - 30 K. It is based on the properties of the Coulomb blockade [4, 5] in one- or two-dimensional arrays of tunnel junctions at temperatures where the charging energy $E_C < k_B T$. Here $E_C = e^2/2C_{\text{eff}}$, where C_{eff} is the effective capacitance of the tunnel junctions [3]. In the CBT method, the first derivative of the current-voltage characteristics (IV-curve) is measured and from the properties of this curve the temperature can be extracted, using only natural constants and a calculable prefactor. The major advantage of the CBT method is the simple electrical measurement and the insensitivity to magnetic field. [6]

In this letter we present an alternative approach which has the advantage of measurement speed. Using the same type of tunnel junction array we can measure the third derivative of the IV-curve. The third derivative has a zero crossing at a voltage which is (to the first order in $E_C/k_B T$) proportional to the temperature. Thus, only one measurement point, the zero crossing, is needed to measure the temperature. With the original method, a full dI/dV vs V curve must be measured.¹

Taking the expression for dI/dV [1] and deriving twice with respect to V the third derivative d^3I/dV^3 can be written, to the first order in $E_C/k_B T$

$$\frac{d^3I}{dV^3} = -\frac{Me}{R_T C_{\text{eff}}} \left(\frac{e}{Nk_B T} \right)^3 g'' \left(\frac{eV}{Nk_B T} \right). \quad (1)$$

Here N and M are the number of tunnel junctions in series and in parallel (in the case of a two-dimensional array) respectively, R_T is the tunnelling resistance of one

junction at voltages well above the Coulomb blockade and $g(x)$ is defined by Pekola *et al.* [1], and can be written

$$g(x) = \frac{(x/2) \coth(x/2) - 1}{2 \sinh^2(x/2)} \quad (2)$$

The function $g''(x)$ becomes

$$g''(x) = \frac{((x/2) \coth(x/2) - 1)(3 \coth^2(x/2) - 2)}{2 \sinh^2(x/2)} \quad (3)$$

Eq. (1) is valid in the limit $E_C \ll k_B T$ and $R_T \gg R_K = h/e^2 \approx 25.8 \text{ k}\Omega$. Lower temperatures and lower tunnelling resistances cause deviations which can be calculated theoretically [2, 7]. In this paper we have taken into account the effects due to low temperature. The deviations due to low resistance were not considered here, but are estimated to be less than 1% in the measurements presented here.

We can calculate the voltage V_0 at the zero-crossing of Eq. (1) numerically and the result is

$$eV_0 = \pm 2.144 N k_B T. \quad (4)$$

At low temperatures (where $k_B T$ approaches E_C) higher order corrections should be included [2, 8]. This gives a correction to the zero crossing in Eq. (1), which is independent of temperature:

$$eV_0 = 2.144 N k_B T - 0.465 N E_C. \quad (5)$$

The sample we have measured was a two-dimensional array of 256×256 tunnel junctions and each junction had an effective capacitance of 2.2 fF and a tunnelling resistance of 17 k Ω . The array was fabricated using standard shadow evaporation [9, 10] of aluminium and in situ oxidation. The measurements were carried out by applying a DC voltage and an additional AC excitation (123 Hz) to

¹There is also a secondary measurement mode where only the zero-bias conductance is measured. This requires calibration of the tunnel junction resistance and capacitance.

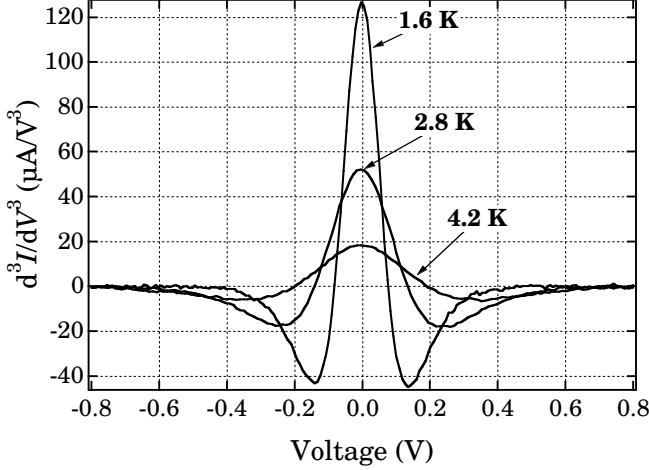


FIG. 1. The third derivative of the IV-curve, d^3I/dV^3 as a function of the voltage, measured at three different temperatures. The voltage V_0 at the zero-crossing scales linearly with the temperature. The sample was a two-dimensional array with 256×256 tunnel junctions.

the sample in series with a resistor R_b with a resistance of $20 \text{ k}\Omega$. The voltage over the resistor was measured with a Stanford SRS830 lock-in amplifier which locked to the third harmonic (369 Hz) of the excitation AC voltage. This signal $\delta V_{3\omega}$ is proportional to the third derivative of the IV-curve. The excitation voltage δV_ω over the sample was measured with another lock-in amplifier which locked to the basic frequency (123 Hz) and the DC voltage was measured with a voltmeter. Additional low-, high- and band-pass filtering was used to improve the measurement.

We used a pumped ^4He cryostat equipped with a vacuum regulator which kept the bath at a constant pressure, and therefore constant temperature, during the measurements.

To find the relation between the third derivative and $\delta V_{3\omega}$ we can make a Taylor expansion of the IV-curve to the third order and arrive at the formula

$$\frac{d^3I}{dV^3} = \frac{24}{R_b} \frac{\delta V_{3\omega}}{\delta V_\omega^3}, \quad (6)$$

where $\delta V_{3\omega}$ and δV_ω are voltage amplitudes (not rms values).

This method requires a relatively large excitation amplitude, comparable to V_0 , which introduces errors due to higher derivatives. Including fifth and seventh orders in the Taylor series we can write

$$\frac{24}{R_b} \frac{\delta V_{3\omega}}{\delta V_\omega^3} = \frac{d^3I}{dV^3} + \frac{\delta V_\omega^2}{16} \frac{d^5I}{dV^5} + \frac{\delta V_\omega^4}{640} \frac{d^7I}{dV^7}. \quad (7)$$

Knowing the amplitude of the excitation δV_ω , the errors due to the higher order terms can be calculated and be corrected for. However, right at the zero crossing of the third derivative the higher order terms are quite small and therefore a relatively large δV_ω can be used without introducing large errors.

Fig. 1 shows a measurement of d^3I/dV^3 at three different temperatures. The shape of the curves follow the

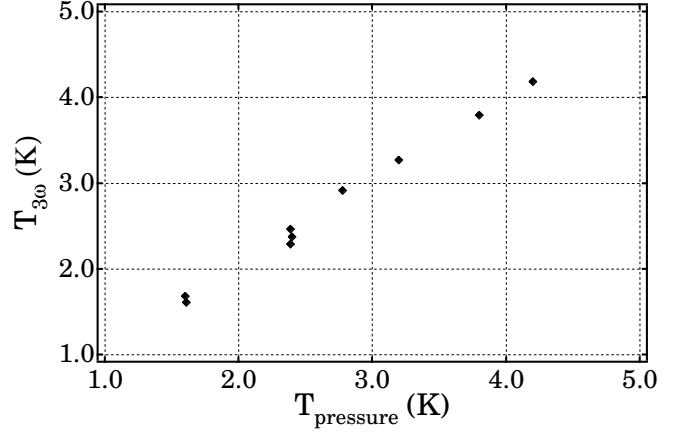


FIG. 2. The temperature calculated from the zero crossing (Eq. 5) versus the temperature determined from the ^4He bath pressure.

expected $g''(x)$ behaviour, and the zero crossing follows Eq. 5 within a few percent. Fig. 2 shows the temperature calculated from the zero crossing plotted against the temperature calculated from the ^4He vapour pressure [11] from 1.6 K to 4.2 K.

To test the principal advantage of this measuring method compared to the one used by Pekola *et al.* we set up a feedback loop, illustrated in Fig. 3. We used a DC output voltage from the lock-in amplifier, which was proportional to the $\delta V_{3\omega}$ signal amplitude, as an error signal to a PID regulator.² The output of the regulator was used as the DC bias voltage and added to the AC excitation provided by the lock-in amplifier. The voltage over a resistor in series with the array was applied to the input of the lock-in amplifier, which was set to extract the third harmonic of the excitation frequency. After we adjusted the PID parameters to proper values, the DC voltage over the array stabilised at the voltage V_0 , as defined by Eq. 5.

As a demonstration that the voltage follows the temperature as expected, we took a time trace of this voltage while we adjusted the temperature in steps, by changing the bath pressure, and the result is the graph in Fig. 4, where the voltage V_0 is converted to temperature using Eq. 5. The temperature steps are evident in the figure, and agrees well with the temperature calculated from the ^4He vapour pressure, except for the lowest step. The disagreement at this step is probably due to higher derivatives and higher order corrections to Eq. 5. [2] At the beginning of the fourth step, at 600 s in Fig. 4, the P gain of the feedback was too large and the signal started to oscillate, but after reducing the gain (at around 680 s in the graph) the signal was stable again. Note that the relatively slow time response is not due to the thermometer or the measurement, but rather due to the time it takes to pump down the pressure in the ^4He bath.

While Fig. 4 shows that this method is working, the precision is not very impressive in this first experiment,

²A PID regulator (**P**roportional, **I**ntegrating and **D**erivating) is a general feedback circuit with three adjustable parameters, which can be used with a wide range of applications.

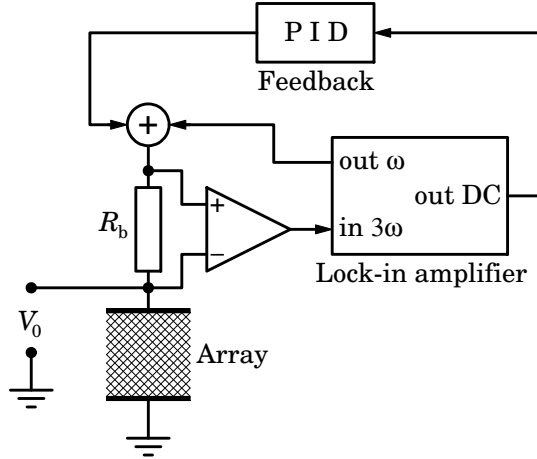


FIG. 3. The feedback loop used to demonstrate our temperature measurement method. The lock-in amplifier generates a sine wave which is added to a DC voltage produced by the PID circuit. This voltage is applied to the sensor in series with a resistor, and the voltage over the resistor is sensed by the lock-in amplifier. The lock-in amplifier is set up to detect the third harmonic of the output frequency, to effectively measure the third derivative of the IV-curve. The DC output voltage is proportional to the amplitude of the detected signal and serves as an input error signal to the PID circuit. With the proper feedback parameters the voltage over the sensor array stabilises at V_0 , as defined in Eq. 5.

with fluctuations up to 10%. However, there are several ways to improve the method. The use of a lock-in amplifier picks up the very weak third harmonic signal below the main excitation signal and the noise, but by notching out the basic frequency before the input we can increase the dynamic range of the amplifier, and get a cleaner signal. The PID parameters can also be better optimised to the measurement, and continuously adjusted.

Looking at Eq. 1, it is obvious that we can make another improvement by increasing M , *i.e.* the number of parallel junctions in the array. The signal amplitude increases linearly with M . This speaks in favour of using 2D arrays with this measurement method. Note that we do not gain anything by decreasing N , the number of junctions in series, because in order to avoid higher order derivatives to affect the measurement we need to decrease the excitation amplitude δV_ω by the same amount. Even though it was not done in this experiment, it would be natural to let δV_ω be proportional to the temperature, to compensate for the strong signal dependence on temperature ($\sim T^{-3}$).

In conclusion, we have measured the third derivative of the IV-curve of a two-dimensional array of tunnel junctions. We show, theoretically and experimentally, that the zero crossing of this curve scales linearly with temperature, to the first order, and provides a primary temperature measurement. We also demonstrate the use of a feedback loop to create a fast primary thermometer. The feedback loop is possible because only one measurement is needed to get at a quantity which is proportional to the temperature.

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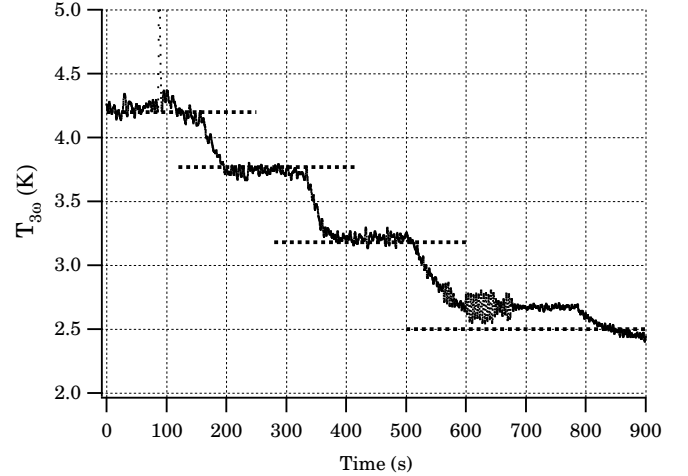


FIG. 4. A time trace of the temperature calculated from the zero-crossing voltage V_0 (Eq. 5) while the temperature was varied in four steps. The dashed horizontal lines represent the temperature calculated from the vapour pressure of ^4He [11]. The agreement is reasonable, except at the lowest temperature where higher order effects and higher derivatives affect the measurement.

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